

YG225C2,N2,D2 (10A)

(200V / 10A)

FAST RECOVERY DIODE

■ Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		250	V
Isolating voltage	V_{iso}	Terminals-to-Case, AC.1min	1500	V
Average output current	I_o	Square wave, duty=1/2, $T_c=95^\circ C$	10*	A
Surge current	I_{FSM}	Sine wave 10ms	70	A
Operating junction temperature	T_j		+150	°C
Storage temperature	T_{stg}		-40 to +150	°C

* Average forward current of centertap full wave connection

- Electrical characteristics ($T_a=25^\circ C$ Unless otherwise specified)

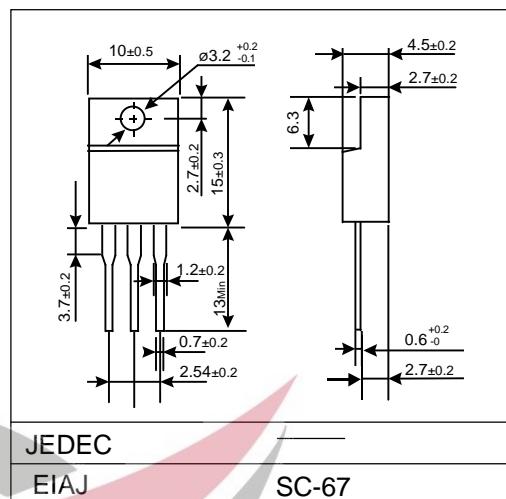
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop **	V_{FM}	$I_{FM}=2.5A$	1.3	V
Reverse current **	I_{RRM}	$V_R=V_{RRM}$	50	µA
Reverse recovery time	trr	$I_f=0.1A, I_r=0.1A, I_{rec}=0.01A$	0.4	µs
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5*	°C/W

- Mechanical characteristics

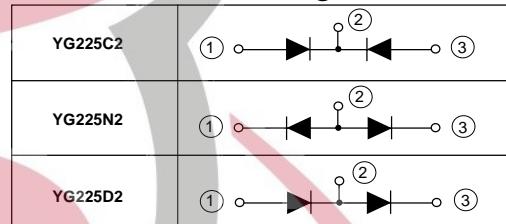
** Rating per element

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate weight		2.3	g

■ Outline drawings, mm

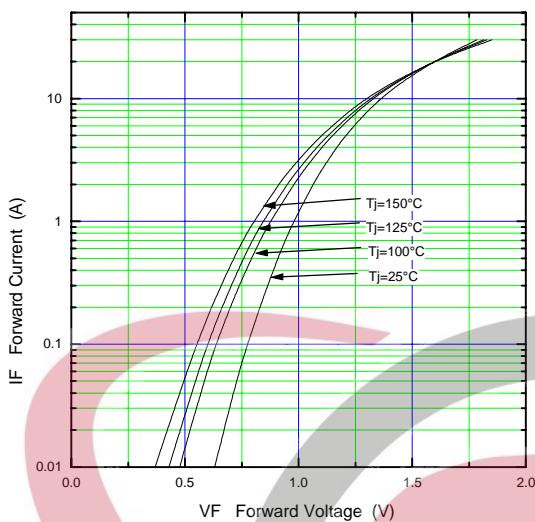


■ Connection diagram

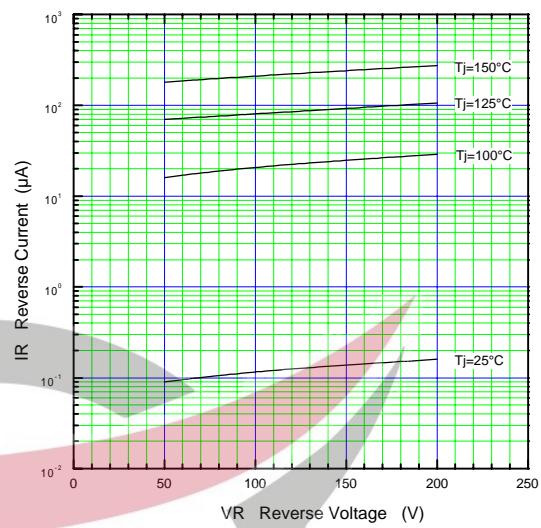


■ Characteristics

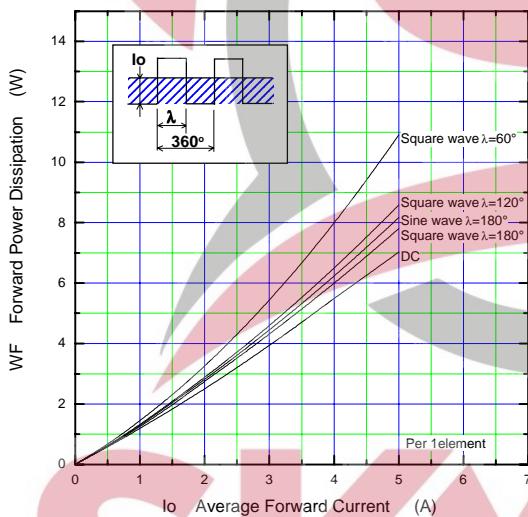
Forward Characteristic (typ.)



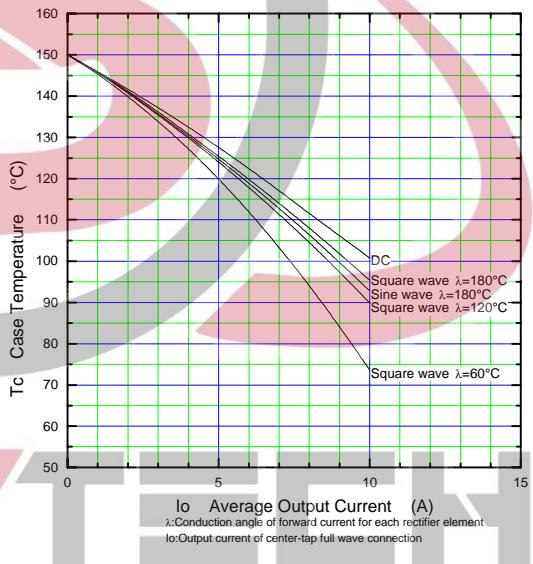
Reverse Characteristic (typ.)



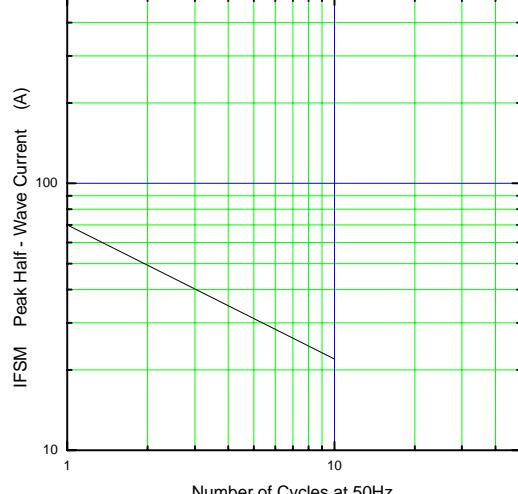
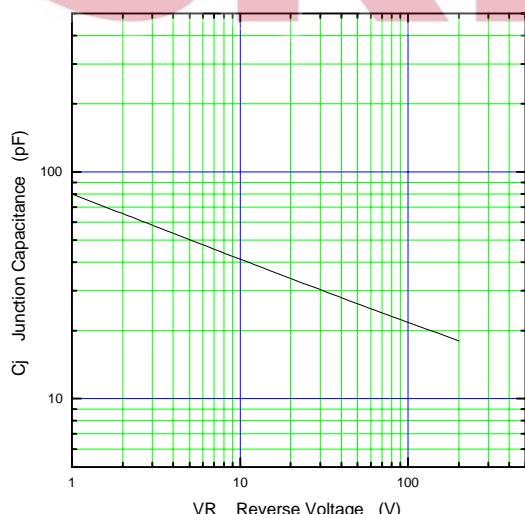
Forward Power Dissipation



Current Derating ($Io-T_c$)



Junction Capacitance Characteristic (typ.)



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Transient Thermal Impedance

